

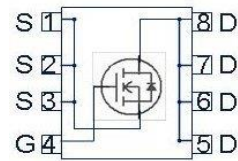
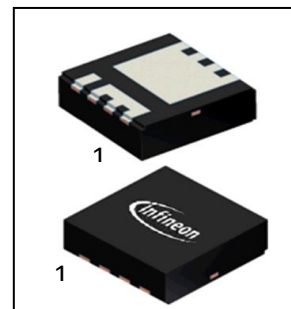
OptiMOS™ -5 Power-Transistor

Product Summary

V_{DS}	100	V
$R_{DS(on),max}$	24	mΩ
I_D	30	A

Features

- OptiMOS™ - power MOSFET for automotive applications
- N-channel - Enhancement mode - Logic Level
- AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green Product (RoHS compliant)
- 100% Avalanche tested
- Feasible for automatic optical inspection (AOI)

PG-TSDSON-8


Type	Package	Marking
IAUZ30N10S5L240	PG-TSDSON-8	5N1L240

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C=25\text{ °C}$, $V_{GS}=10\text{V}$	30	A
		$T_C=100\text{ °C}$, $V_{GS}=10\text{V}^{1)}$	22	
Pulsed drain current ¹⁾	$I_{D,pulse}$	$T_C=25\text{ °C}$	120	
Avalanche energy, single pulse ¹⁾	E_{AS}	$I_D=12\text{A}$	17	mJ
Avalanche current, single pulse	I_{AS}	-	12	A
Gate source voltage	V_{GS}	-	±20	V
Power dissipation	P_{tot}	$T_C=25\text{ °C}$ $T_J=175\text{ °C}$	45.5	W
Operating and storage temperature	T_j , T_{stg}	-	-55 ... +175	°C
IEC climatic category; DIN IEC 68-1	-	-	55/175/56	-

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics¹⁾						
Thermal resistance, junction - case	R_{thJC}	-	-	-	3.3	K/W
Thermal resistance, junction - ambient	R_{thJA}	6 cm ² cooling area ²⁾	-	-	62	

Electrical characteristics, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=1mA$	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=15\mu A$	1.2	1.7	2.2	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V, T_j=25^\circ C$	-	-	1	μA
		$V_{DS}=100V, V_{GS}=0V, T_j=125^\circ C^{1)}$	-	-	100	
Gate-source leakage current	I_{GSS}	$V_{GS}=20V, V_{DS}=0V$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=15A$	-	26	31	m Ω
		$V_{GS}=10V, I_D=15A$	-	19.5	24	
Gate resistance ¹⁾	R_G		-	1.5	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics¹⁾

Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=50V,$ $f=1MHz$	-	640	832	pF
Output capacitance	C_{oss}		-	113	147	
Reverse transfer capacitance	C_{rss}		-	7.9	11.8	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=50V, V_{GS}=10V,$ $I_D=30A, R_G=3.5\Omega$	-	2	-	ns
Rise time	t_r		-	1	-	
Turn-off delay time	$t_{d(off)}$		-	4.6	-	
Fall time	t_f		-	3.4	-	

Gate Charge Characteristics¹⁾

Gate to source charge	Q_{gs}	$V_{DD}=50V, I_D=15A,$ $V_{GS}=0 \text{ to } 10V$	-	2.1	2.7	nC
Gate to drain charge	Q_{gd}		-	1.9	2.9	
Gate charge total	Q_g		-	9.5	14	
Gate plateau voltage	$V_{plateau}$		-	3.3	-	V

Reverse Diode

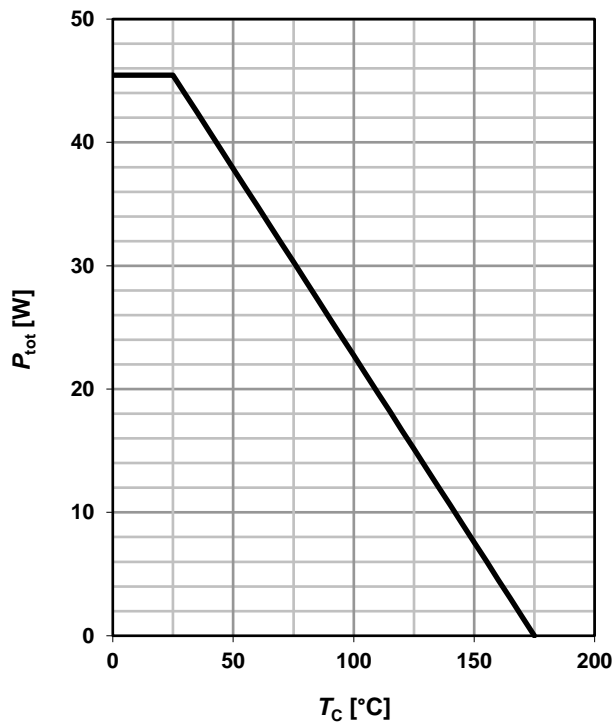
Diode continuous forward current ¹⁾	I_S	$T_C=25^\circ C$	-	-	30	A
Diode pulse current ¹⁾	$I_{S,pulse}$		-	-	120	
Diode forward voltage	V_{SD}	$V_{GS}=0V, I_F=15A,$ $T_j=25^\circ C$	-	0.9	1.1	V
Reverse recovery time ¹⁾	t_{rr}	$V_R=50V, I_F=30A,$ $di_F/dt=100A/\mu s$	-	37	-	ns
Reverse recovery charge ¹⁾	Q_{rr}		-	34	-	nC

¹⁾ Specified by design. Not subject to production test.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

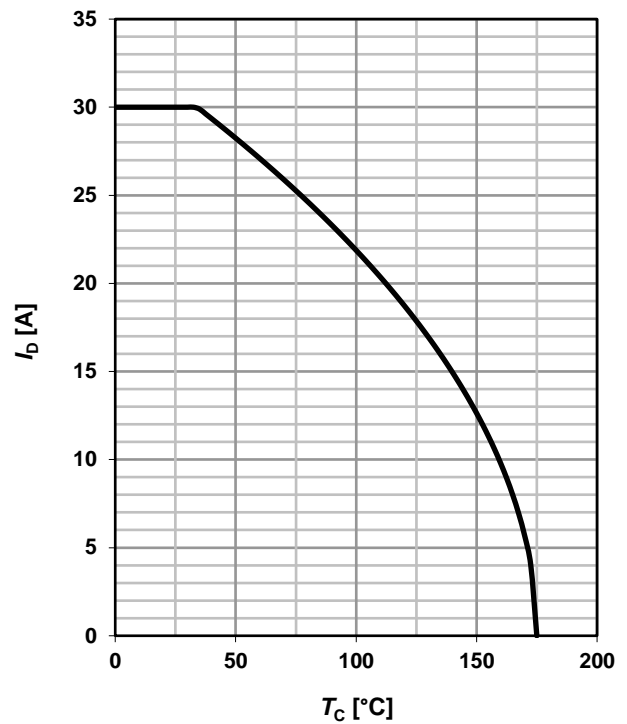
1 Power dissipation

$$P_{\text{tot}} = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



2 Drain current

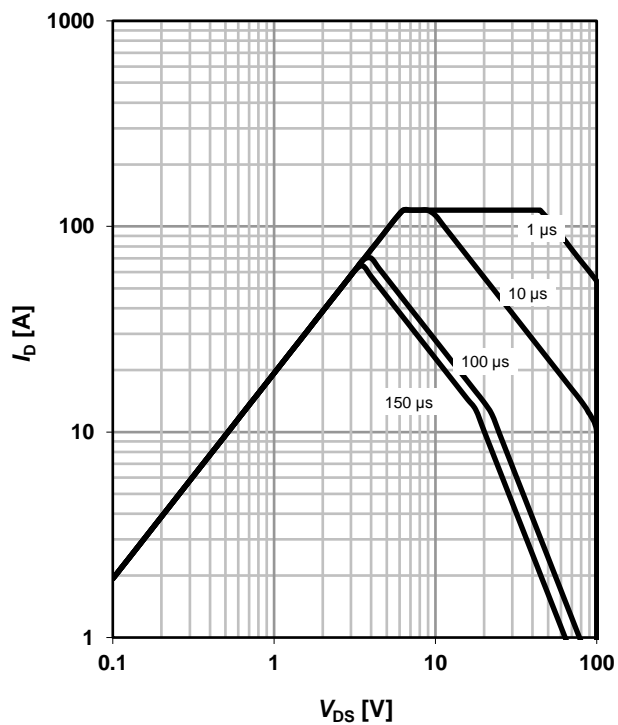
$$I_D = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_C = 25 \text{ °C}; D = 0$$

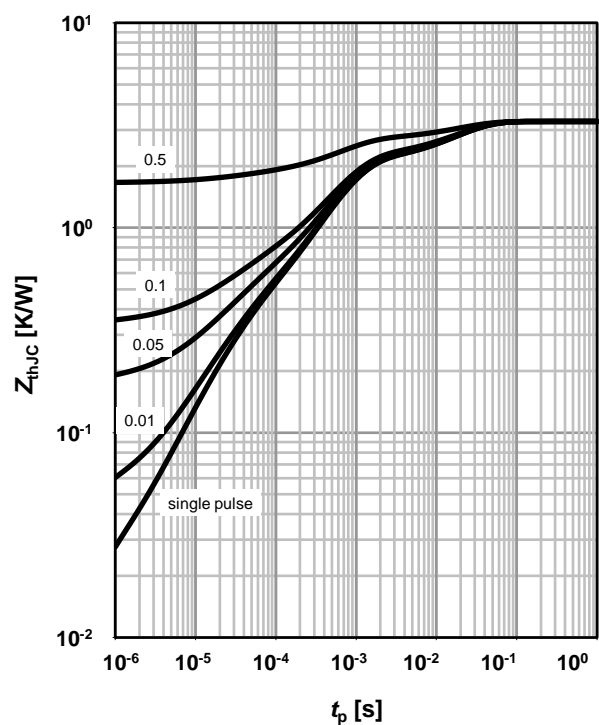
parameter: t_p



4 Max. transient thermal impedance

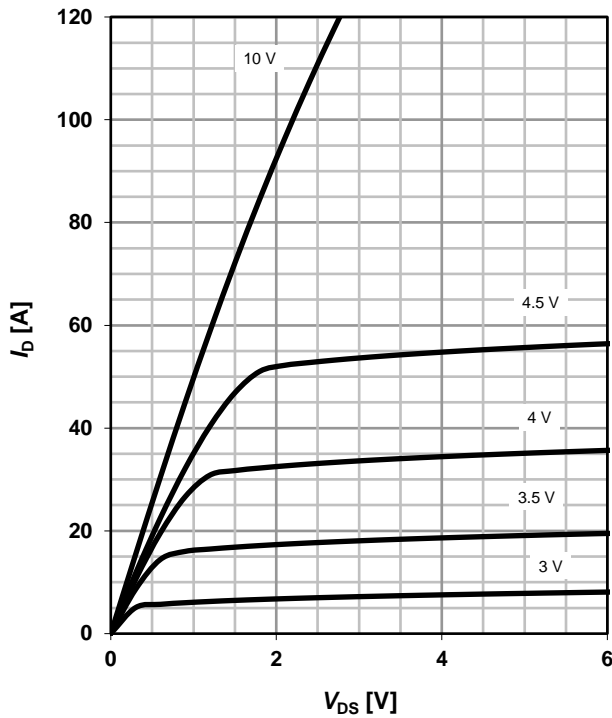
$$Z_{\text{thJC}} = f(t_p)$$

parameter: $D = t_p/T$

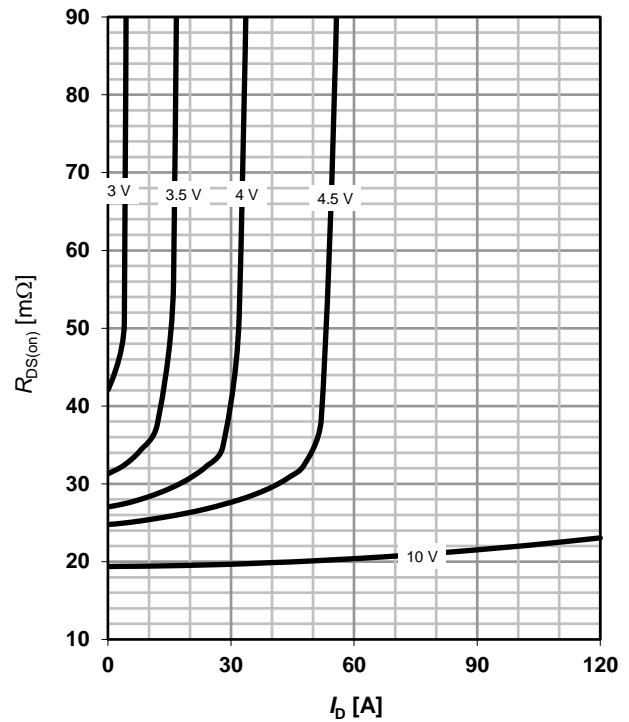


5 Typ. output characteristics

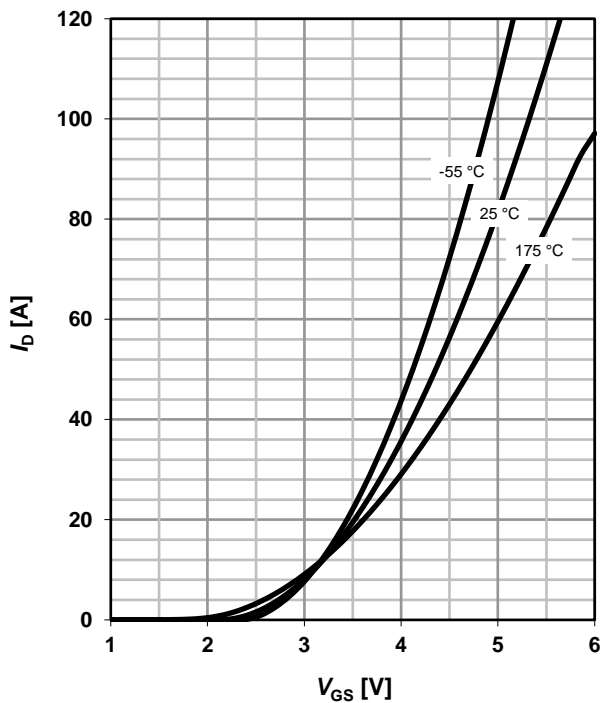
$$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$$

 parameter: V_{GS}

6 Typ. drain-source on-state resistance

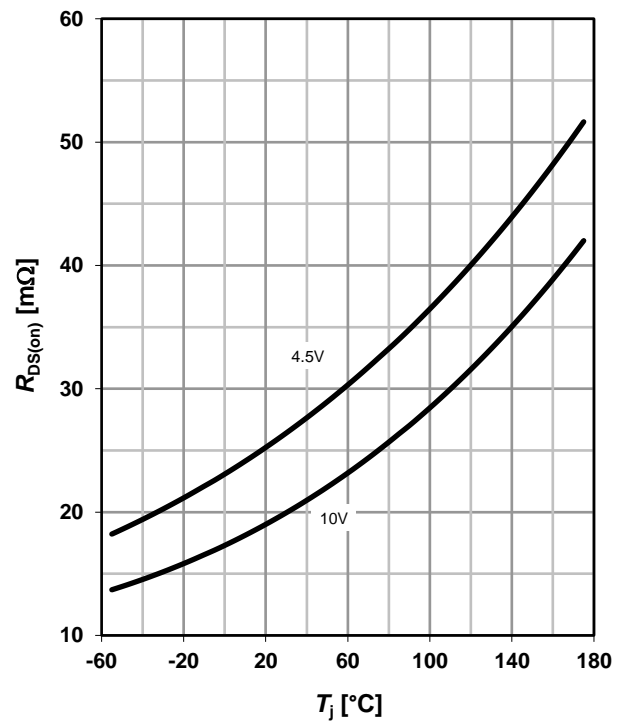
$$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$$

 parameter: V_{GS}

7 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} = 6V$$

 parameter: T_j

8 Typ. drain-source on-state resistance

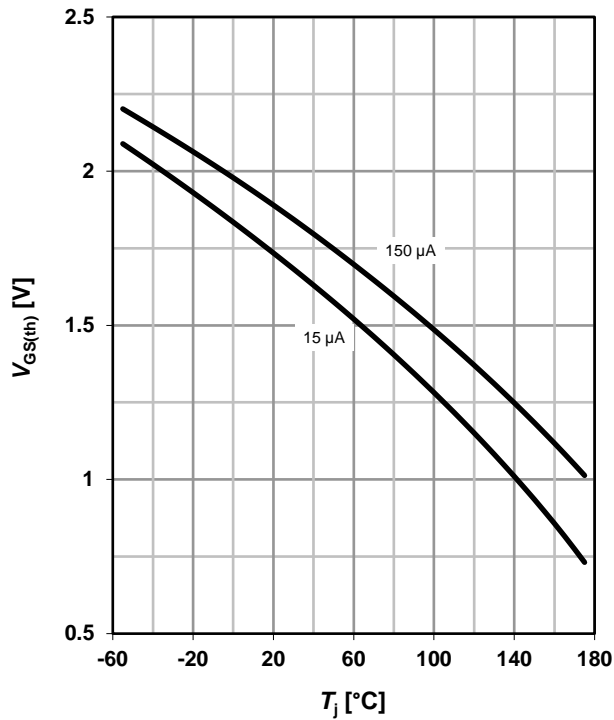
$$R_{DS(on)} = f(T_j); I_D = 15A$$

 parameter: V_{GS}


9 Typ. gate threshold voltage

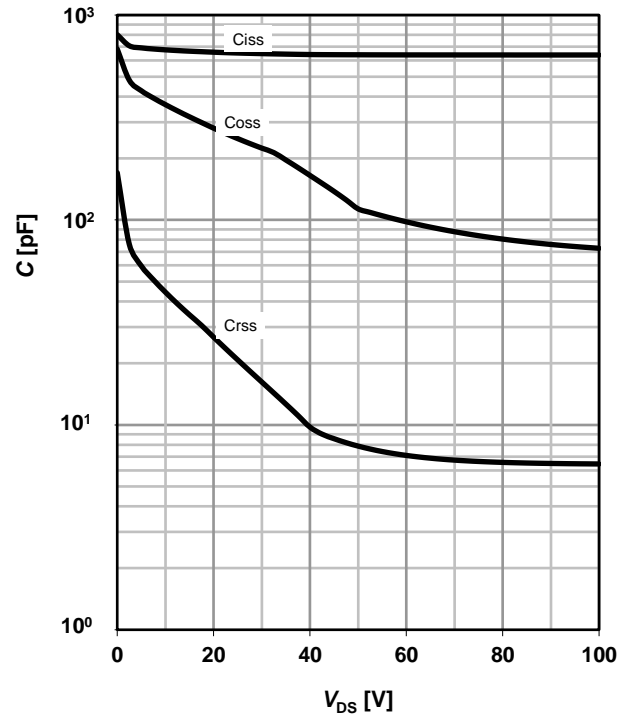
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter: I_D



10 Typ. capacitances

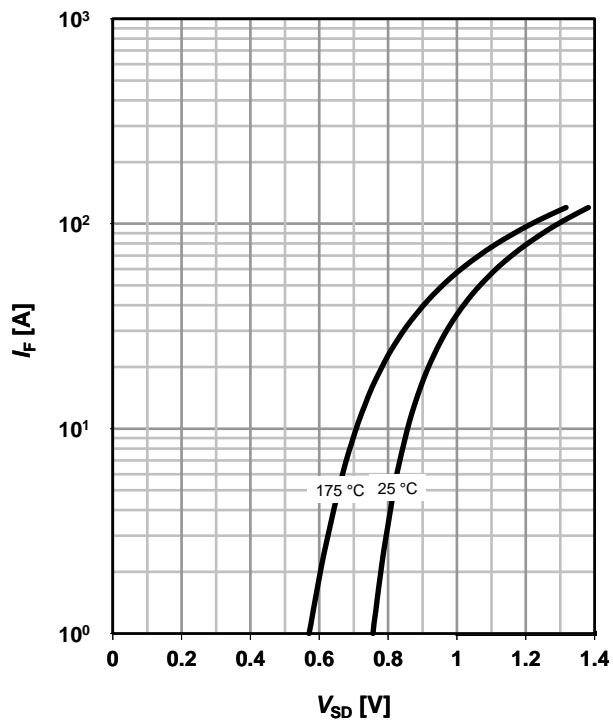
$C = f(V_{DS}); V_{GS} = 0 V; f = 1 MHz$



11 Typical forward diode characteristics

$I_F = f(V_{SD})$

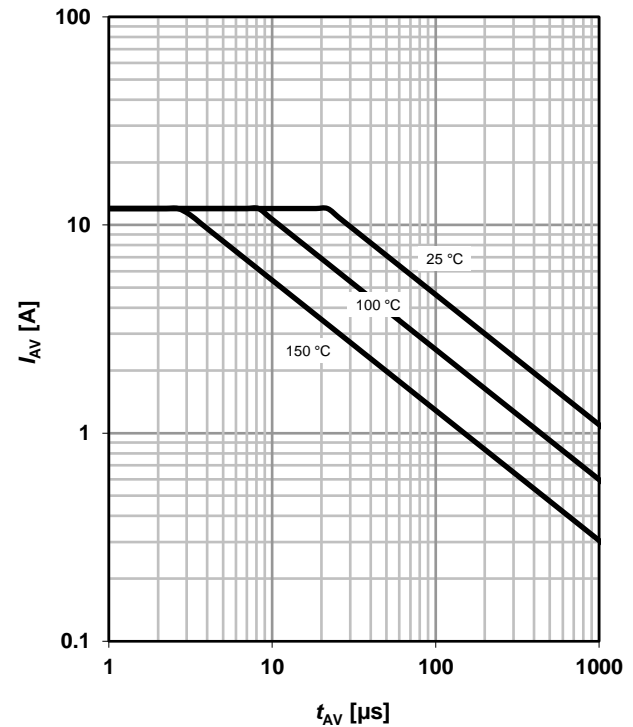
parameter: T_j



12 Avalanche characteristics

$I_{AS} = f(t_{AV})$

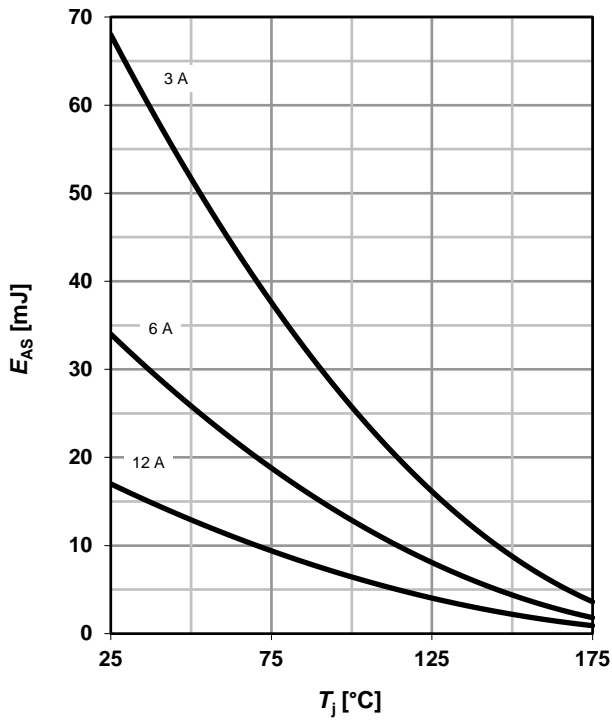
parameter: $T_{j(start)}$



13 Avalanche energy

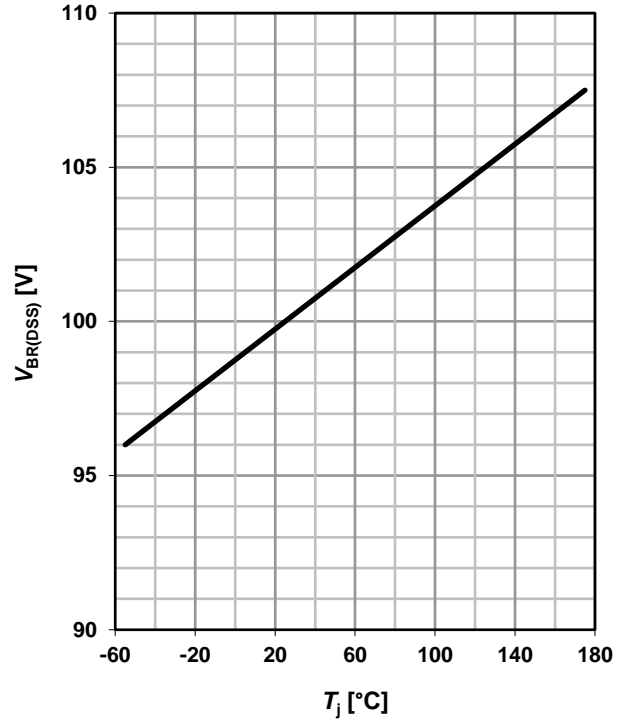
$$E_{AS} = f(T_j)$$

parameter: I_D



14 Drain-source breakdown voltage

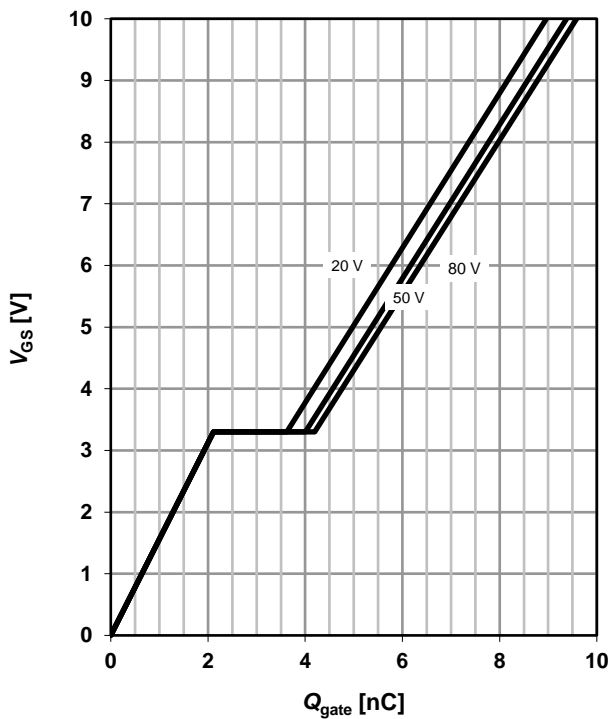
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$



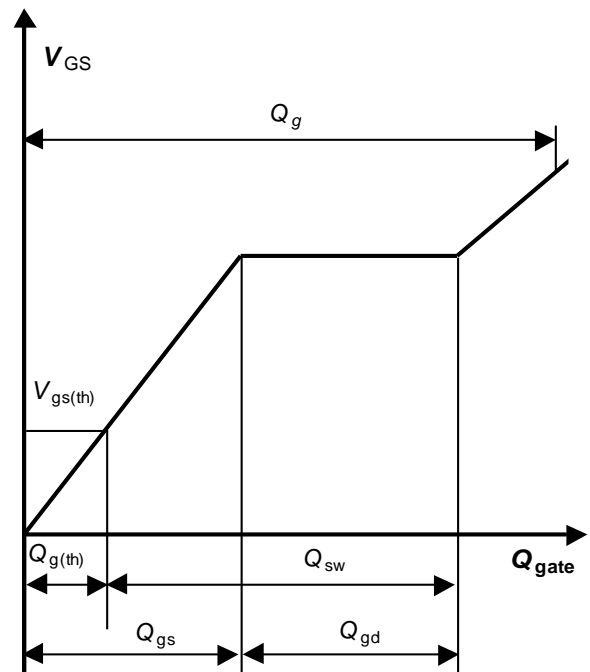
15 Typ. gate charge

$$V_{GS} = f(Q_{gate}); I_D = 15 \text{ A pulsed}$$

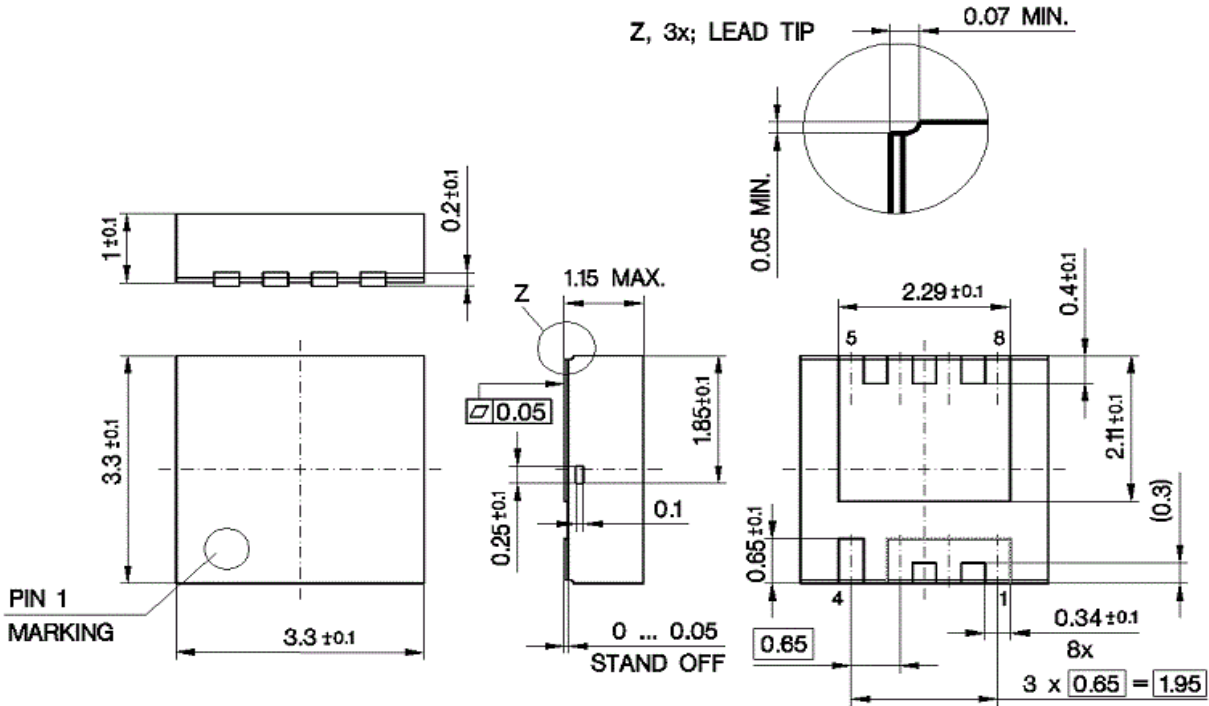
parameter: V_{DD}



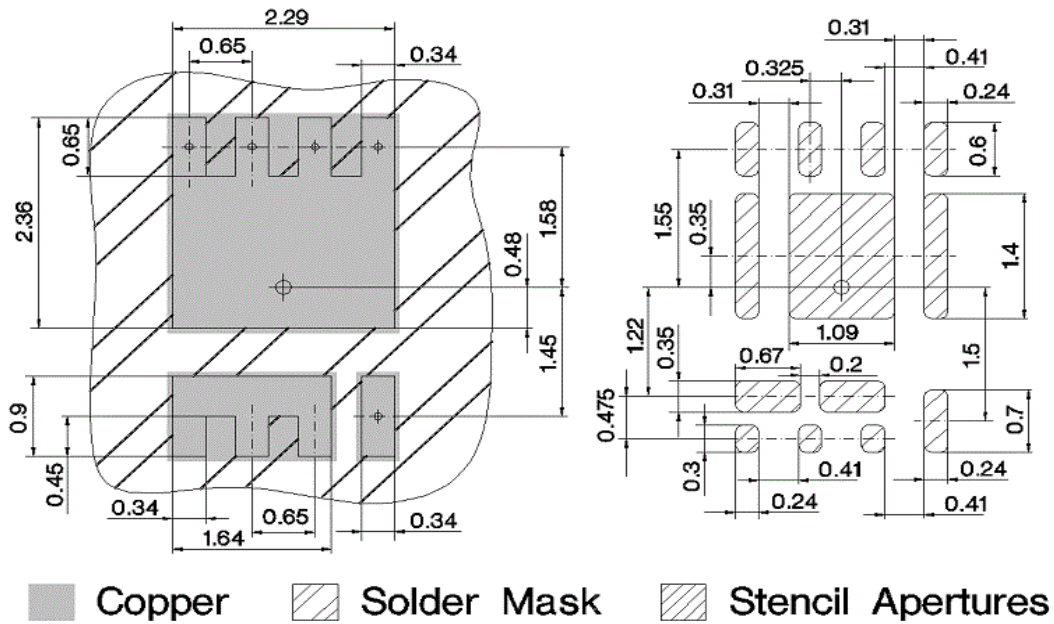
16 Gate charge waveforms



PG-TSDSON-8: Outline

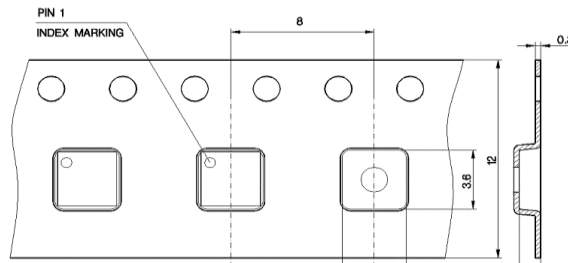


Footprint



Dimensions in mm

Packaging



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If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

Revision History

Version	Date	Changes
Revision 1.0	23.07.2019	Final Data Sheet